

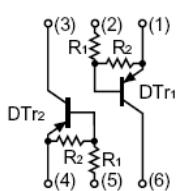
dual digital transistors (PNP+PNP)

FEATURES

- Two DTA114E chips in a package
- Mounting possible with SOT-563 automatic mounting machines
- Transistor elements are independent, eliminating interference
- Mouting cost and area be cut in half

Marking: B11

Equivalent circuit



Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Value	Units
V_{cc}	Supply Voltage	-50	V
$I_{C(\text{MAX})}$	Output current	-100	mA
V_i	Input voltage	-40 to +10	V
P_D	Power dissipation	150	mW
T_J	Junction temperature	150	°C
T_{stg}	Storage temperature	-55~+150	°C

Electrical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Input turn-on voltage	$V_{i(\text{on})}$	$V_O=-0.3\text{V}$, $I_O=-10\text{ mA}$	-3			V
Input cut-off voltage	$V_{i(\text{off})}$	$V_{cc}=-5\text{V}$, $I_O=-100\mu\text{A}$			-0.5	V
Output voltage	$V_{O(\text{on})}$	$I_O=-10\text{ mA}$, $I_i=-0.5\text{ mA}$			-0.3	V
Input cut-off current	I_i	$V_i=-5\text{V}$			-0.88	mA
Output cut-off current	$I_{O(\text{off})}$	$V_{cc}=-50\text{V}$, $V_i=0$			-0.5	μA
DC current gain	G_i	$V_O=-5\text{V}$, $I_O=-5\text{mA}$	30			
Transition frequency	f_T	$V_O=-10\text{V}$, $I_O=-5\text{mA}$, $f=100\text{MHz}$		250		MHz
Input resistance	R_1		7		13	$\text{k}\Omega$
Resistance ratio	R_2/R_1		0.8		1.2	

